

1 A Three-quadrant triacs high commutation Rev. 03 — 10 September 2007

Product data sheet

1. Product profile

1.1 General description

Passivated, guaranteed commutation triacs in a plastic package. The 'sensitive gate' E and ER series are intended for interfacing with low power drivers, including microcontrollers. The high commutation B series are designed to commutate the full RMS current at the maximum junction temperature without the aid of a snubber.

1.2 Features

- Suitable for interfacing with low power drivers, including microcontrollers
 Applications
 - Motor controls

1.4 Quick reference data

- I_{TSM} \leq 12.5 A
- V_{DRM} ≤ 600 V (BTA201-600B)
- V_{DRM} ≤ 600 V (BTA201-600E)
- V_{DRM} ≤ 800 V (BTA201-800B)
- V_{DRM} ≤ 800 V (BTA201-800E)
- V_{DRM} ≤ 800 V (BTA201-800ER)

- Solenoid drivers
- I_{T(RMS)} ≤ 1 A
 I_{GT} ≤ 50 mA (BTA201-600B)
- I_{GT} ≤ 10 mA (BTA201-600E)
- I_{GT} ≤ 50 mA (BTA201-800B)
- I_{GT} ≤ 10 mA (BTA201-800E)
- $I_{GT} \le 10 \text{ mA} (BTA201-800 \text{ ER})$

2. Pinning information

Pin	Description	Simplified outline	Symbol
B and E ser	•		-,
1	main terminal 2 (T2)		T2-T1
2	gate (G)	Цлд	sym051
3	main terminal 1 (T1)	ĨĨĨ	
ER series			
1	main terminal 1 (T1)	321	
2	gate (G)	SOT54 (TO-92)	
3	main terminal 2 (T2)		



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3. Ordering information

Table 2. Orde	ring inform	ation						
Type number	Package	Package						
	Name	Description	Version					
BTA201-600B	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54					
BTA201-600E								
BTA201-800B								
BTA201-800E								
BTA201-800ER								

4. Limiting values

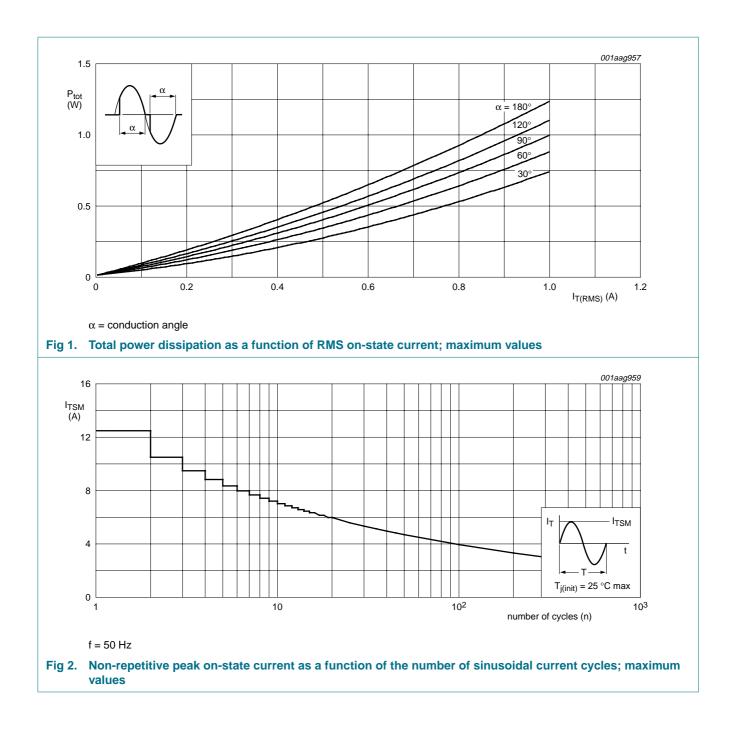
Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage				
		BTA201-600B	<u>[1]</u> _	600	V
		BTA201-600E	<u>[1]</u> _	600	V
		BTA201-800B	-	800	V
		BTA201-800E	-	800	V
		BTA201-800ER	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{lead} \le 54.3 \text{ °C}$; see Figure 4 and 5	-	1	А
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_j = 25 \text{ °C prior to}$ surge; see <u>Figure 2</u> and <u>3</u>			
		t = 20 ms	-	12.5	А
		t = 16.7 ms	-	13.7	А
l²t	I ² t for fusing	t = 10 ms	-	0.78	A ² s
dl _T /dt	rate of rise of on-state current	$\begin{split} I_{TM} &= 1.5 \text{ A}; \text{ I}_{G} = 0.2 \text{ A}; \\ dI_{G}/dt &= 0.2 \text{ A}/\mu\text{s} \end{split}$	-	100	A/μs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	125	°C

 Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 6 A/µs.

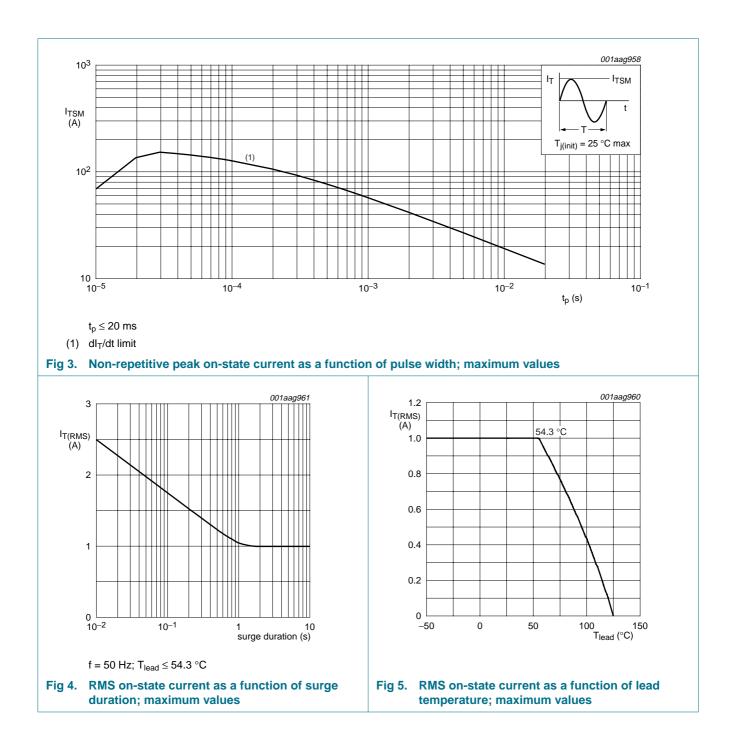
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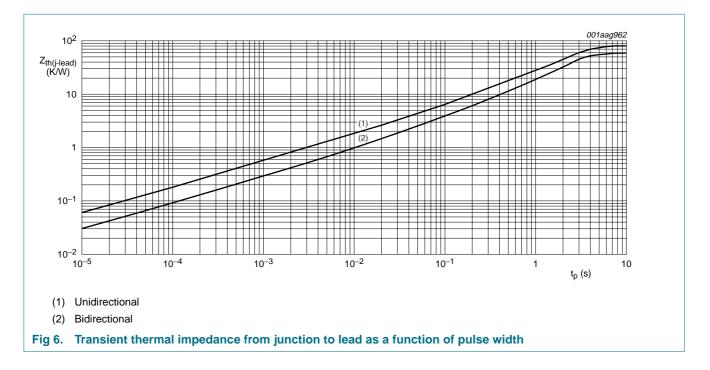


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5. Thermal characteristics

Table 4.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-lead)}$	thermal resistance from junction to lead	full cycle; see Figure 6	-	-	60	K/W
		half cycle; see Figure 6	-	-	80	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	printed-circuit board mounted; lead length = 4 mm	-	150	-	K/W



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6. Static characteristics

Table 5. Static characteristics

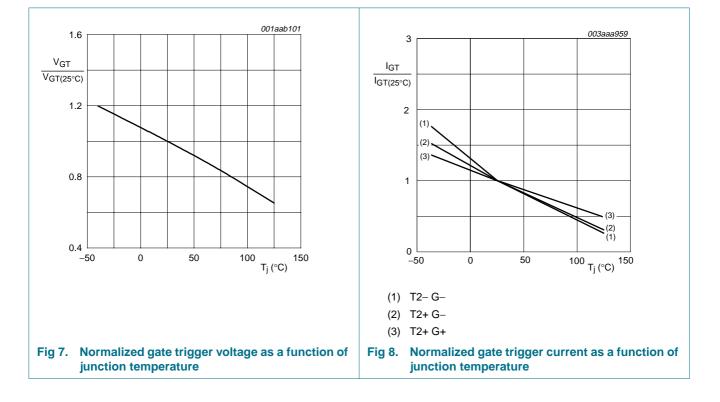
 $T_i = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions	BTA201-600B BTA201-800B		BTA201-600E BTA201-800E BTA201-800ER			Unit	
			Min	Тур	Max	Min	Тур	Мах	
I _{GT}	gate trigger current	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ see}$ Figure 8							
		T2+ G+	-	-	50	-	-	10	mA
		T2+ G–	-	-	50	-	-	10	mA
		T2– G–	-	-	50	-	-	10	mA
IL latching cu	latching current	$V_D = 12 \text{ V}; I_{GT} = 0.1 \text{ A}; \text{see}$ Figure 10							
		T2+ G+	-	-	30	-	-	12	mA
		T2+ G-	-	-	50	-	-	20	mA
		T2– G–	-	-	30	-	-	12	mA
Ι _Η	holding current	V _D = 12 V; I _{GT} = 0.1 A; see <u>Figure 11</u>	-	-	30	-	-	12	mA
VT	on-state voltage	$I_T = 1.4 \text{ A}$; see Figure 9	-	1.2	1.5	-	1.2	1.5	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ see}$ Figure 7	-	0.7	1.5	-	0.7	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A};$ $T_j = 125 \text{ °C}$	0.2	0.3	-	0.2	0.3	-	V
I _D	off-state current	$V_D = V_{DRM(max)};$ $T_j = 125 \ ^{\circ}C$	-	0.1	0.5	-	0.1	0.5	mA

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7. Dynamic characteristics

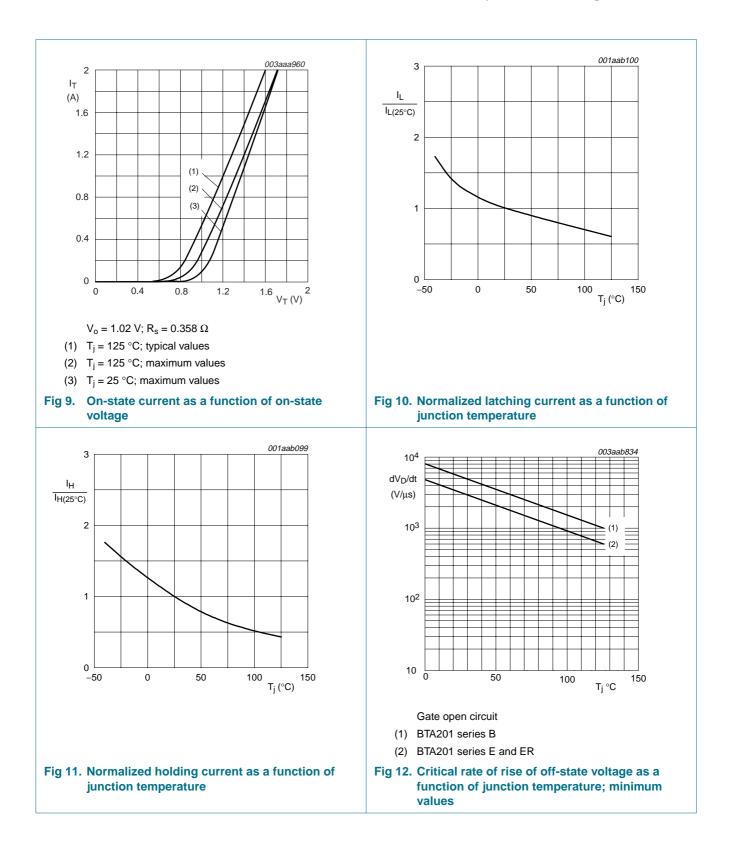
Table 6.	. Dynamic characteristics								
Symbol	Parameter	Conditions		BTA201-600B BTA201-800B			BTA201-600E BTA201-800E BTA201-800ER		
			Min	Тур	Max	Min	Тур	Max	
dV _D /dt	rate of rise of off-state voltage	$V_{DM} = 67 \% V_{DRM(max)};$ T _j = 125 °C; exponential waveform; gate open circuit	1000	-	-	600	-	-	V/μs
dl _{com} /dt	rate of change of commutating current	$V_{DM} = 400 \text{ V}; T_j = 125 \text{ °C};$ $dV_{com}/dt = 20 \text{ V}/\mu s;$ gate open circuit	12	-	-	2.5	-	-	A/ms
		$V_{DM} = 400 \text{ V}; T_j = 125 \text{ °C};$ $dV_{com}/dt = 10 \text{ V}/\mu s;$ gate open circuit	16	-	-	3.5	-	-	A/ms
t _{gt}	gate-controlled turn-on time	$\begin{split} I_{TM} &= 20 \text{ A}; \\ V_D &= V_{DRM(max)}; \\ I_G &= 0.1 \text{ A}; \\ dI_G/dt &= 5 \text{ A}/\mu \text{s} \end{split}$	-	2	-	-	2	-	μs



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8. Package outline

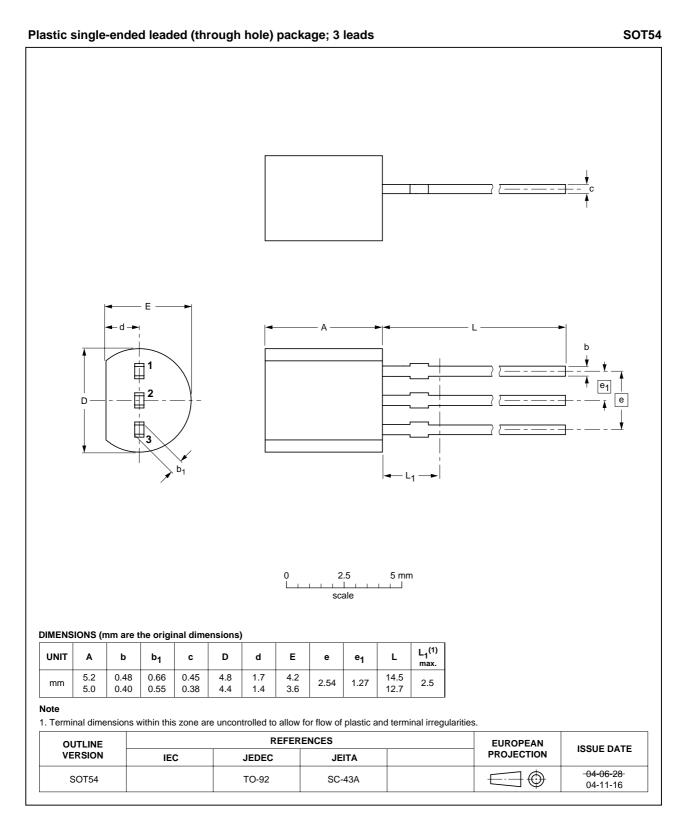


Fig 13. Package outline SOT54 (TO-92)

BTA201_SER_B_E_ER_3
Product data sheet

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9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BTA201_SER_B_E_ER_3	20070910	Product data sheet	-	BTA201_SER_B_E_ER_2		
Modifications:		t of this data sheet has bee of NXP Semiconductors.	en redesigned to com	ply with the new identity		
	 Legal texts 	s have been adapted to the	new company name	where appropriate.		
	 Descriptive 	e titles have been corrected				
	Table 3 "Li	miting values" on page 2: o	dI _T /dt uprated.			
	 Table 6 "Dynamic characteristics" on page 7: dV_D/dt uprated. 					
		"Critical rate of rise of off-s values" on page 8: graph u		tion of junction temperature		
BTA201_SER_B_E_ER_2	20060113	Product data sheet	-	BTA201_SER_B_E_ER_1		
Modifications:	 Figure 4: F 	Figure note corrected				
	 Table 6 "D 	ynamic characteristics" on	page 7: Units corrected	ed		
	 Figure 12: 	Figure title corrected				
BTA201_SER_B_E_ER_1 (9397 750 15154)	20050825	Product data sheet	-	-		

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10. Legal information

10.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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